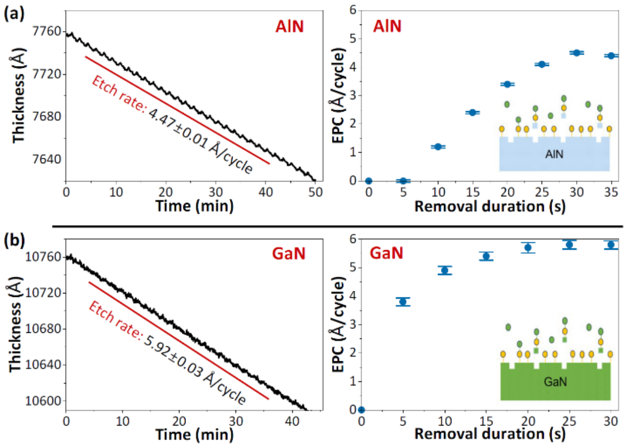

Fig. 1 Etch rates and saturation curves of single-crystalline (a) AlN and (b) GaN

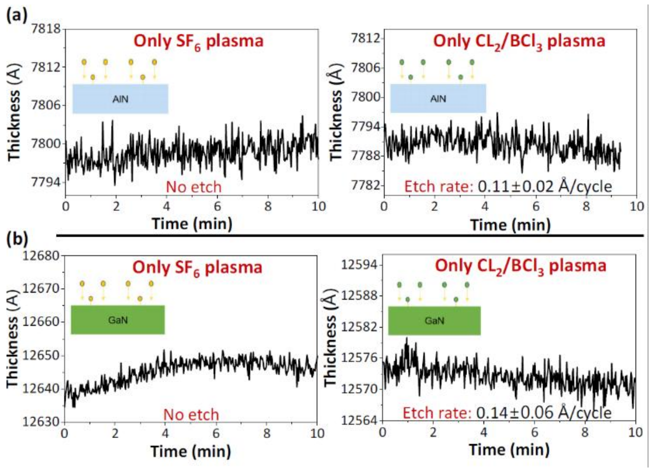

Fig. 2 Isolated half-reactions for (a) AlN and (b) GaN

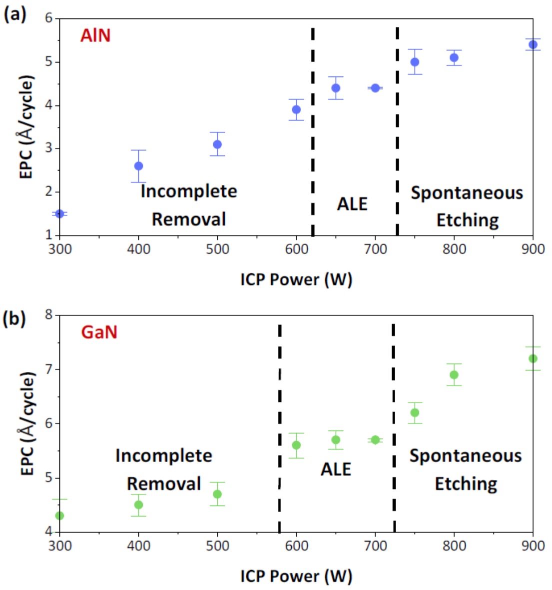

Fig. 3 Effect of ICP power on the EPC of (a) AlN and (b) GaN

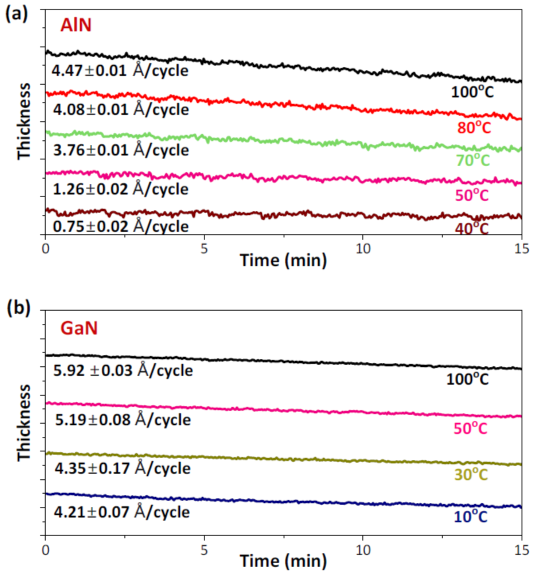

Fig. 4 Temperature dependence of EPC of (a) AlN and (b) GaN

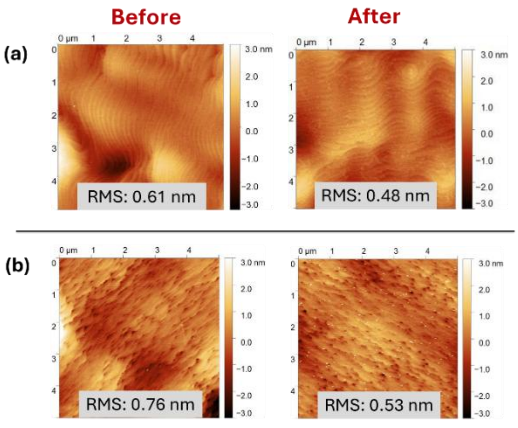

Fig. 5 5 x 5 µm^2 AFM scans before and after 30 cycles of ALE of (a) AlN and (b) GaN

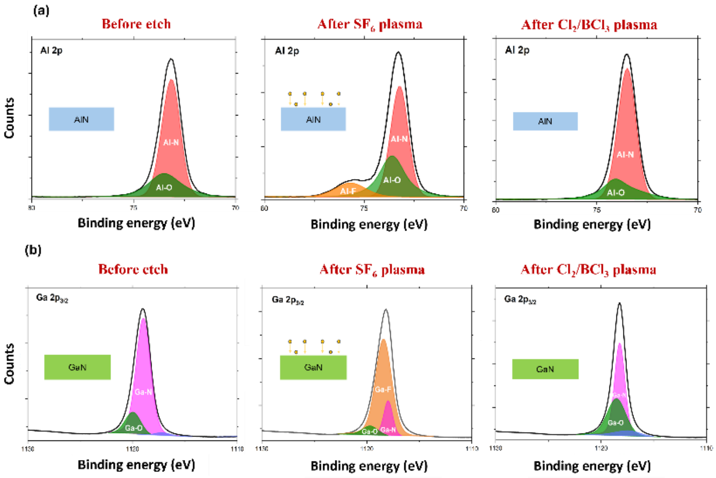

Fig. 6 XPS analysis of etch mechanism